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Electronic Supplementary Information

SiTe Monolayers: Si-Based Analogues of Phosphorene

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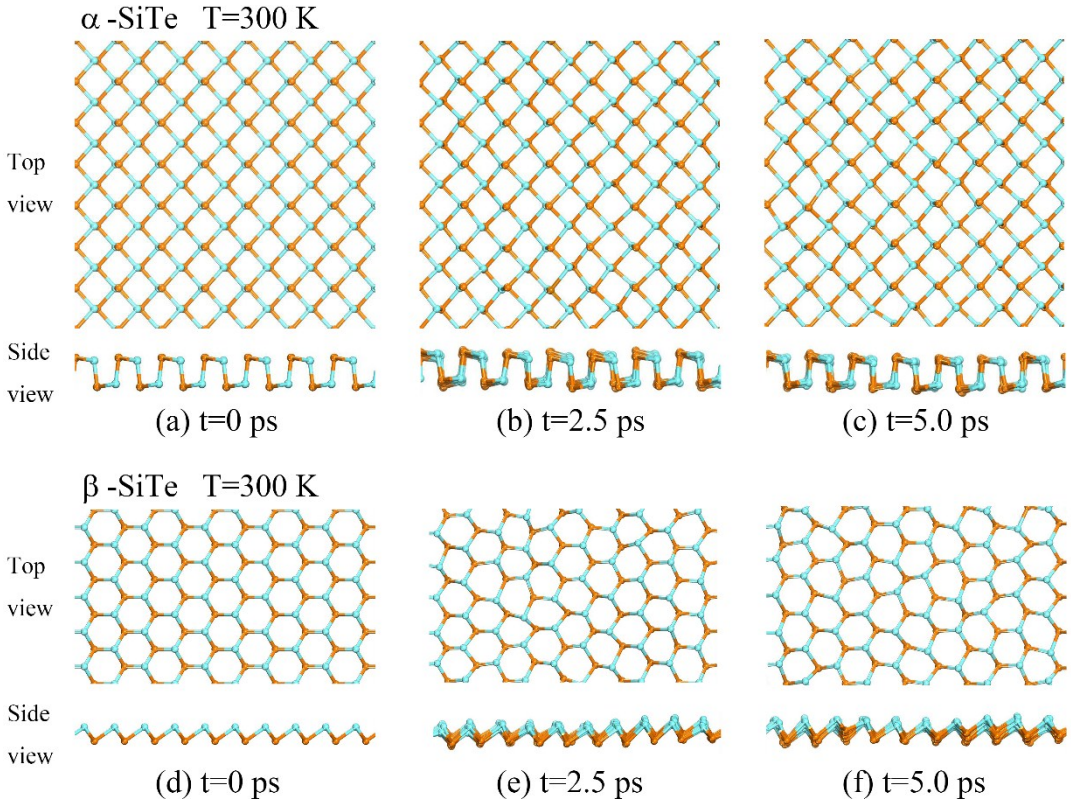

Fig. S1 Snapshots depicting structural changes in α-SiTe (a-c) and β-SiTe (d-f) monolayers in the AIMD simulations at 300K. The initial and final geometries are shown in (a) and (c) for α-SiTe monolayer, and (d) and (f) for β-SiTe monolayer, respectively.